INFORMATION ABOUT THE 2nd MIDTERM EXAM

Additional Office Hours: (in addition to regular office hours, of which there are plenty)

- Kieran Peleaux  9:30-11 a.m. on Thursday, Nov. 8
- Qianyi Xie  11 a.m.-12:30 p.m. on Thursday, Nov. 8
- Prof. Nguyen  2-3:30 p.m. on Thursday, Nov. 8

Review Session:

During the discussion sections on Wednesday, Nov. 7.

Date of Exam:

Friday, Nov. 9, 5-6:30 p.m. (sharp)

Place:

277 Cory

General Information:

The exam will be closed book, but you can have one 8.5”×11” sheet on which you can write anything you would like on both sides of the paper. Bring a calculator to the exam. The exam will contain enough space to put all your work on its sheets. Show and include all your work on the exam sheets. The exam will consist of a few problems, each with a number of parts.

During the exam, make appropriate engineering decisions and approximations in order to simplify your analyses so that you can do the problems quickly and with fewer errors.

Material to be Covered:

Reading in Sedra & Smith, class lecture notes, handouts, labs, and homeworks. The exam is meant to include all material covered so far in the class, but has a sharper focus on more recent material. You might pay more attention to the following areas:

1. The concept of large and small signals and the need for small signal analysis. Large and small signal models for bipolar and MOS transistors and determination of small signal elements/parameters.
2. Biasing of BJT and MOS amplifiers: parameter independent biasing.
3. Frequency response calculations using open- and short-circuit time constants.
4. Analysis of transistor amplifiers, for such parameters as mid-band gain, mid-band small-signal resistances, and frequency response characteristics.
5. Design of the common emitter amplifier. This entails choosing resistors and capacitors to satisfy a given specification.